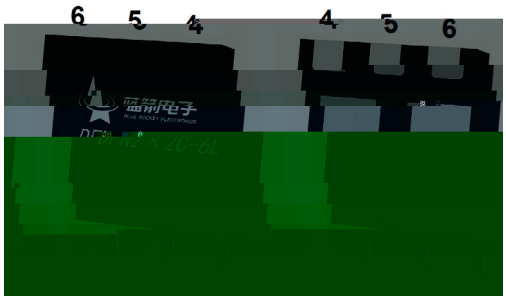
DFN2×2C-6L

Complementary Enhancement MOSFET in a DFN2×2C-6L Plastic Package.

N-channel	P-channel
$V_{DS(V)}$=16V	$V_{DS(V)}$=-16V
I_D=8.4A	I_D=-6.3A
$R_{DS(ON)}$@4.5V≤15mΩ(Typ.13mR)	$R_{DS(ON)}$@-4.5V≤25mΩ(Typ.21mR)
$R_{DS(ON)}$@2.5V≤18mΩ(Typ.16mR)	$R_{DS(ON)}$@-2.5V≤35mΩ(Typ.28mR))
HF Product.	

Power Management in Notebook Computer,Portable Equipment and Battery Powered Systems.

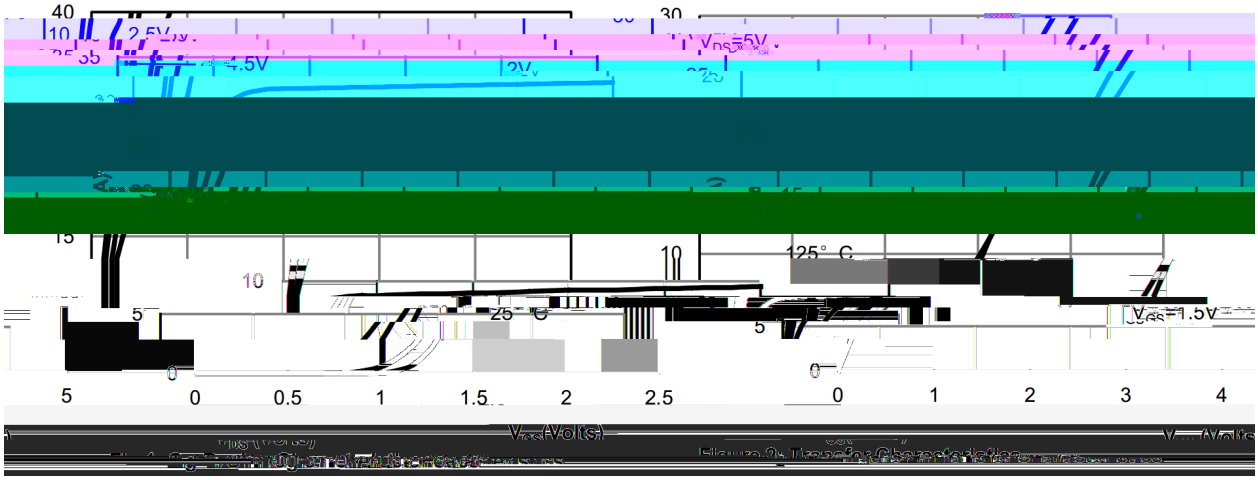


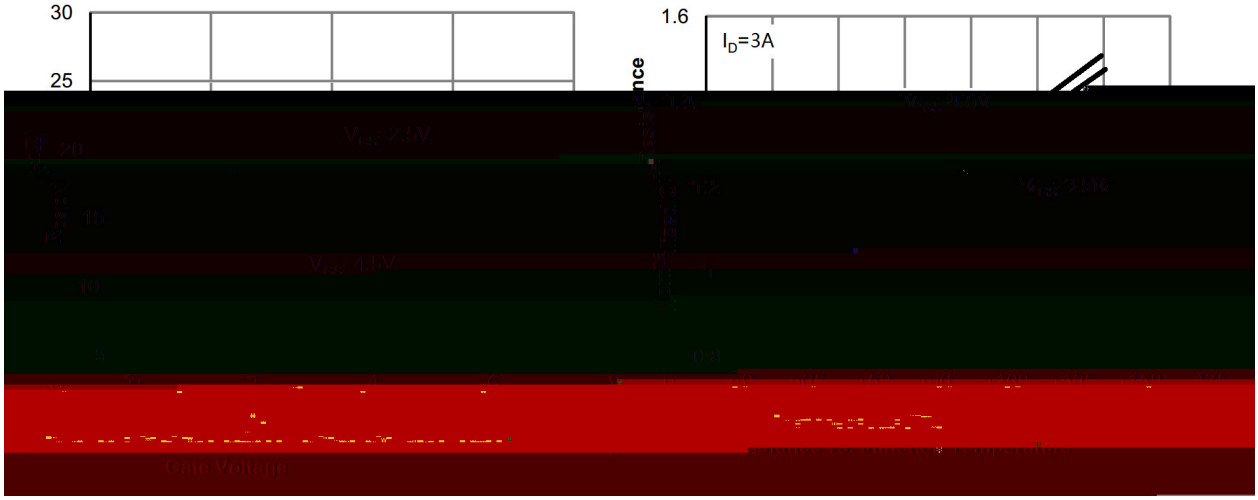
出脚	定义
PIN 1	S1
PIN 2	G1
PIN 3	D2
PIN 4	S2
PIN 5	G2
PIN 6	D1

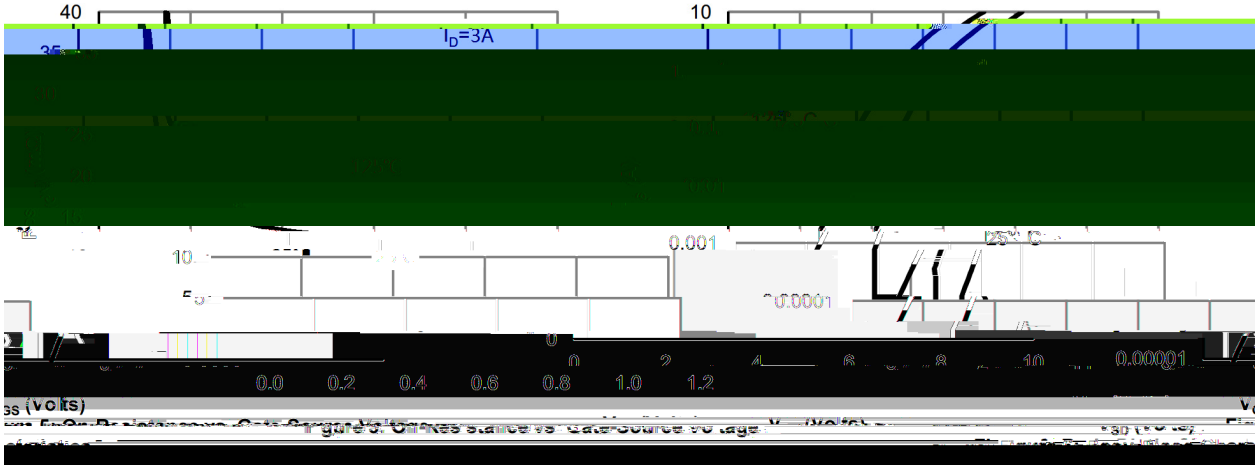
See Marking Instructions.

Parameter	Symbol	Rating		Unit
		N-channe	P-channell	
Drain-Source Voltage	V_{DSS}	±16		V
Gate-Source Voltage	V_{GSS}	±10		V
Continuous Drain Current	I_D	8.4	-6.3	A
Pulsed Drain Current	I_{DM}	33	-24.5	A
Avalanche Current(L=0.1mH)	I_{AS}	7	14	A
Avalanche energy(L=0.1mH)	E_{AS}	6.5	26	mJ
Power Dissipation	P_D	1.6	1.5	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$($t \leq 10s$)	78	83	/W
	$R_{\theta JA}$(Steady-State)	135		

N-

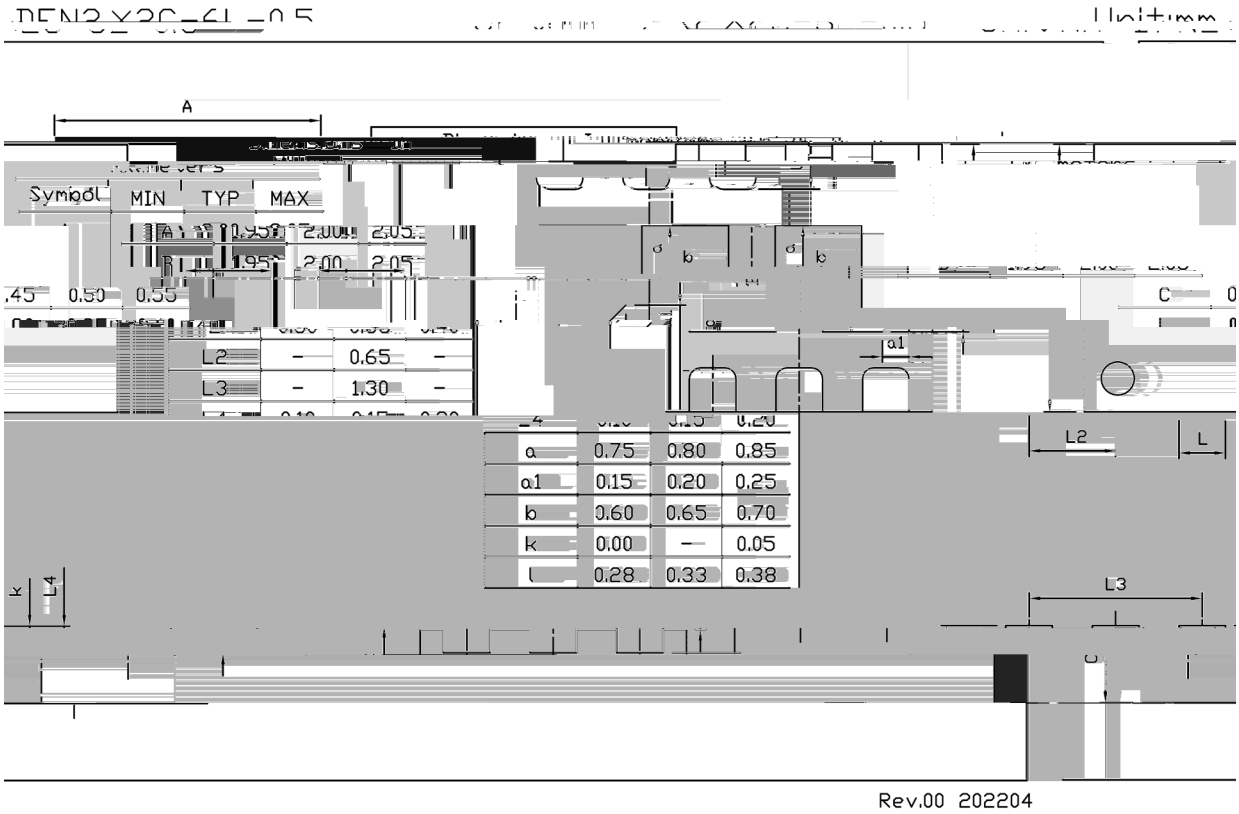

40
30
4.5V
2V
V_{DS}=5V
10
125° C
25° C
V_{GS}=1.5V
5
0
0.5
1
1.5
2
2.5
3
4
V_{GS}(Volts)


30
25
1.6
I_D=3A
V_{GS}=2.5V
V_{GS}=4.5V
Gate Voltage


40
I_D=3A
10
0.001
0.0001
0.00001
0.0
0.2
0.4
0.6
0.8
1.0
1.2
(Volts)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

P-



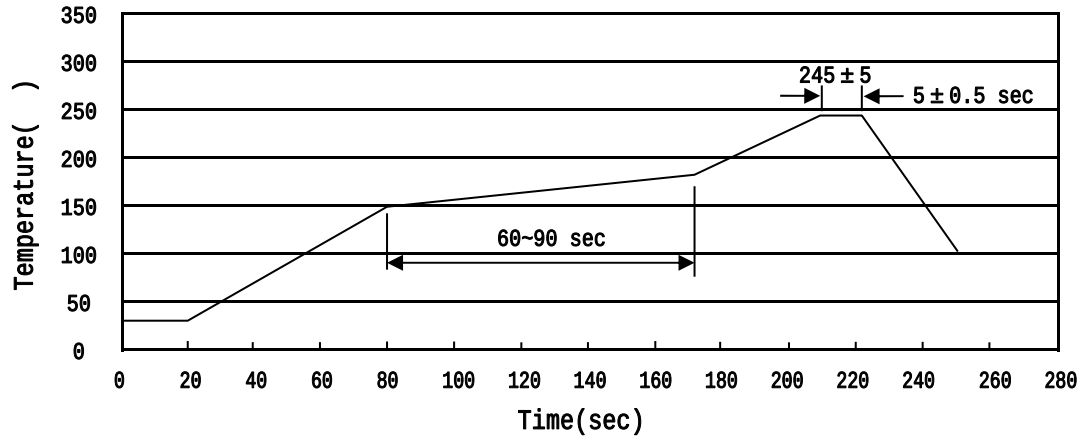
Rev.00 202204

BR
150C016
****

Note:

BR:	Company Code
150C016:	Product Type
****:	Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)



				Note:	
1	150	180	60	90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5			5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3			2	10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm³)
DFN 2×2C-6L	4,000	10	40,000	4	160,000	7 ×8	210×205×205	445×435×230